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TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π -MOSV)

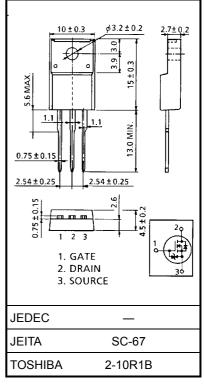
2SK2679

Chopper Regulator, DC–DC Converter and Motor Drive Applications

- Low drain-source ON resistance $: R_{DS} (ON) = 0.84 \Omega (typ.)$
- High forward transfer admittance $|Y_{fs}| = 4.4 \text{ S (typ.)}$
- Low leakage current $: I_{DSS} = 100 \ \mu A \ (max) \ (V_{DS} = 400 \ V)$
- Enhancement-mode : $V_{th} = 2.0 \sim 4.0 \text{ V} (V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA})$

Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	400	V	
Drain-gate voltage (R	_{GS} = 20 kΩ)	V _{DGR}	400	V	
Gate-source voltage		V _{GSS}	±30	V	
Drain current	DC (Note 1)	۱ _D	5.5	А	
	Pulse (Note 1)	I _{DP}	22	А	
Drain power dissipation	n (Tc = 25°C)	PD	35	W	
Single pulse avalanche	e energy (Note 2)	E _{AS}	223	mJ	
Avalanche current		I _{AR}	5.5	А	
Repetitive avalanche e	energy (Note 3)	E _{AR}	3.5	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature ra	ange	T _{stg}	-55~150	°C	



Weight: 1.9 g (typ.)

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch−c)}	3.57	°C / W
Thermal resistance, channel to ambient	R _{th (ch−a)}	62.5	°C / W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 12 mH, R_G = 25 Ω , I_{AR} = 5.5 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution. Unit: mm

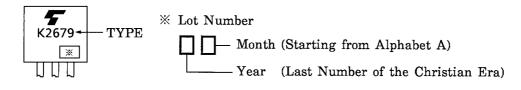
Electrical Characteristics (Ta = 25°C)

Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GSS}	V _{GS} = ±25 V, V _{DS} = 0 V	_		±10	μA
Gate-source bro	eakdown voltage	V (BR) GSS	I _G = ±10 μA, V _{DS} = 0 V	±30	_	_	V
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 400 V, V _{GS} = 0 V	_	-	100	μA
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	400	_	_	V
Gate threshold v	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0		4.0	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 3 A		0.84	1.2	Ω
Forward transfe	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 3 A	2.0	4.4	_	S
Input capacitance	ce	C _{iss}			720	_	pF
Reverse transfe	erse transfer capacitance C_{rss} V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz		V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		80	_	
Output capacitance		Coss			250	_	
Switching time	Rise time	tr	$V_{GS} \stackrel{10V}{}_{0V} \stackrel{I_{D}=2A}{}_{0V} \stackrel{V_{out}}{}_{0V} \stackrel{V_{out}}{}_{RL} = 100\Omega$	_	15	_	
	Turn-on time	t _{on}		_	30	_	
	Fall time	t _f		_	25	_	ns
	Turn-off time	t _{off}	Duty $\leq 1\%$, t _w =10 μ s	_	110	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	17	_	
Gate-source charge		Q _{gs}	V _{DD} ≈ 320 V, V _{GS} = 10 V, I _D = 5.5 A		10		nC
Gate-drain ("miller") Charge		Q _{gd}			7	—	

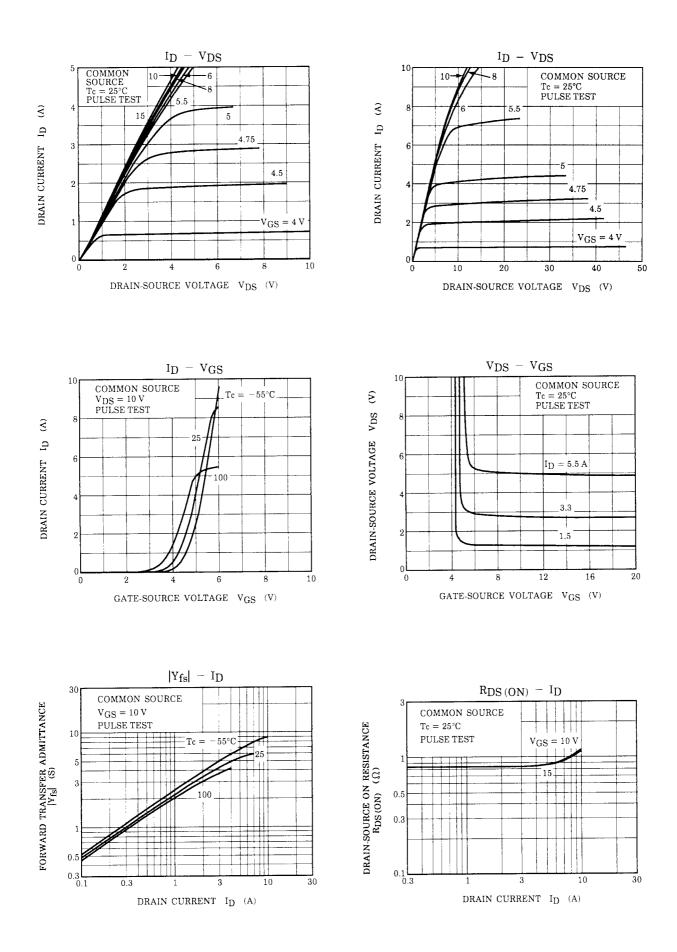
Source–Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	-	_	_	5.5	А
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	22	A
Forward voltage (diode)	V _{DSF}	I _{DR} = 5.5 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 5.5 A, V _{GS} = 0 V		350	—	ns
Reverse recovery charge	Q _{rr}	dI _{DR} / dt = 100 Å / µs	_	2.1	—	μC

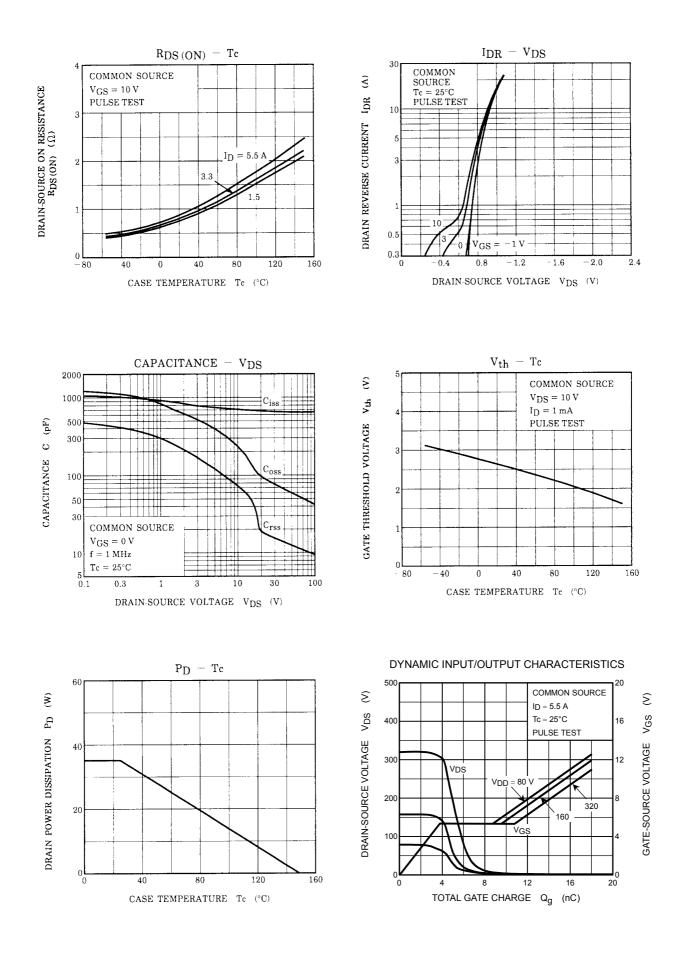
Marking

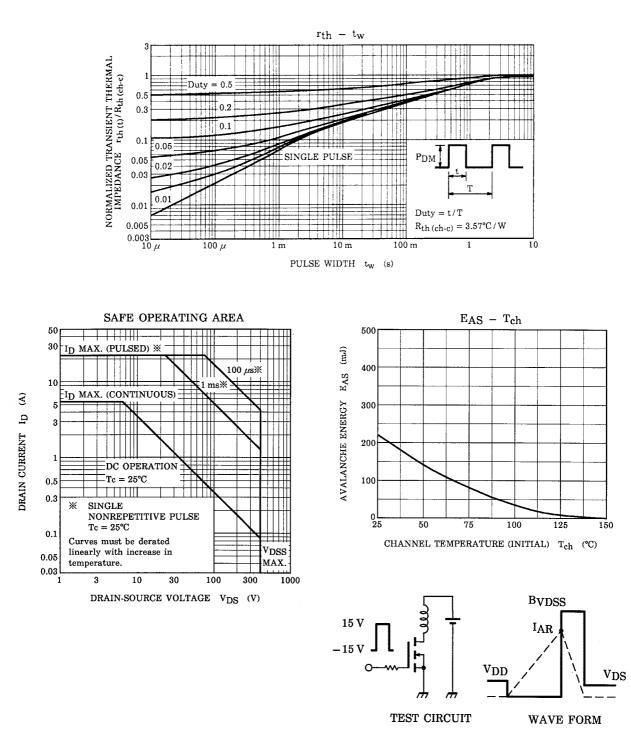


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